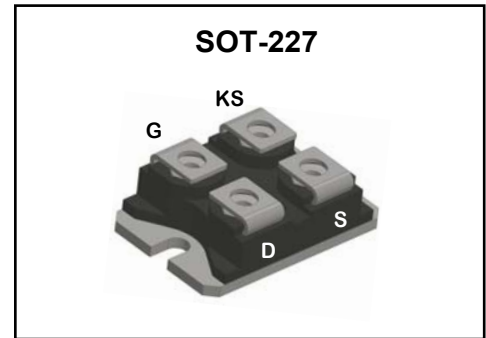
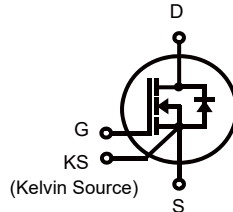


SiC MOSFET Power Module

Features

- ◆ $V_{DSS} = 1200V$
- ◆ $R_{DS(ON)}$ typ. $6m\Omega @ V_{GS} = 18V$
- ◆ High speed switching with low capacitances
- ◆ Easy to parallel and simple to drive
- ◆ Real Kelvin Source Connection
- ◆ Pb Free & RoHS Compliant
- ◆ Electrically Isolation base plate

Preliminary



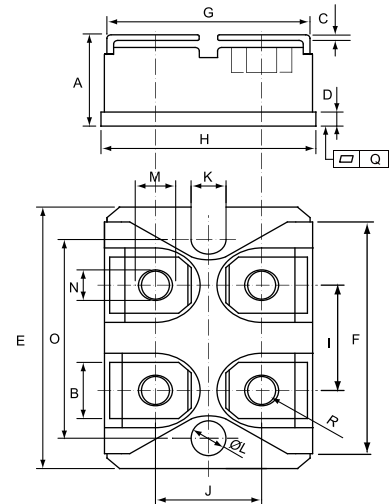
Dimensions in inches and (millimeters)

Applications

- ◆ Solar Inverters
- ◆ UPS
- ◆ Motor Drive
- ◆ Induction heating
- ◆ Switch Mode Power Supplies
- ◆ Battery Chargers
- ◆ DC/DC Converters

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	1200	V
Gate-Source Voltage (dynamic)	$V_{GS(max)}$	-10/+23	V
Gate-Source Voltage (static)	$V_{GS(OP)}$	-4/+18	V
Drain Current-Continuous	I_D	$370 @ T_c = 25^\circ C$ $250 @ T_c = 100^\circ C$	A
Drain Current-Pulsed	I_{DM}	740	A
Maximum Power Dissipation	P_D	1000	W
Storage Temperature Range	T_{STG}	-40 to +125	$^\circ C$
Operating Junction Temperature Range	T_{VJ}	-40 to +175	$^\circ C$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.15	$^\circ C/W$
Isolation Voltage (A.C. 1 minute) between All Terminals and Baseplate	V_{iso}	2500	V
Mounting torque (M4 Screw)	To heatsink To terminals	M_d	1.3 1.1 N_m



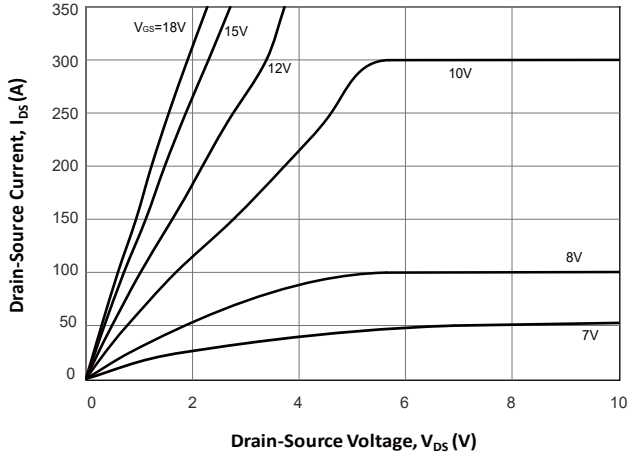
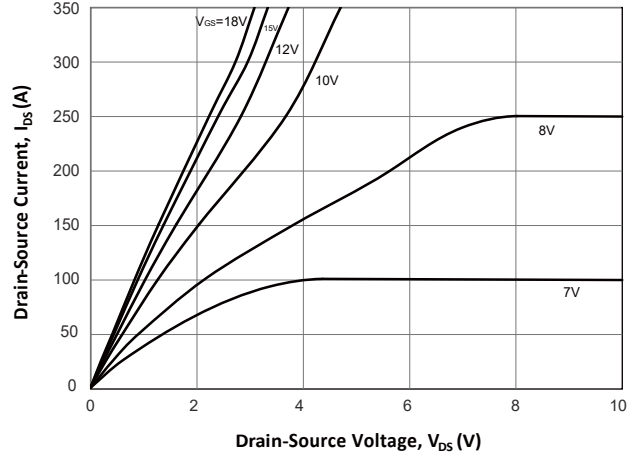
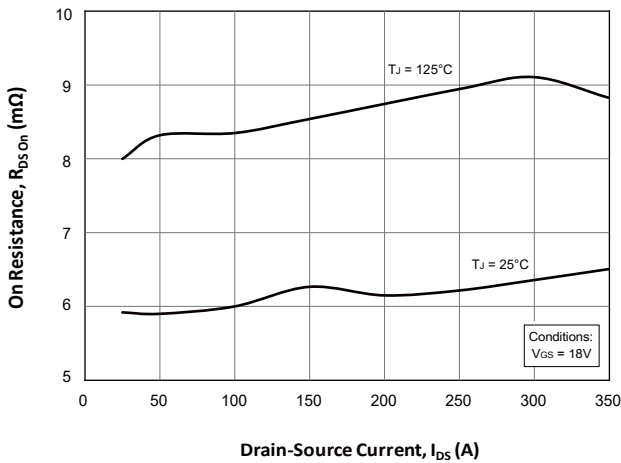
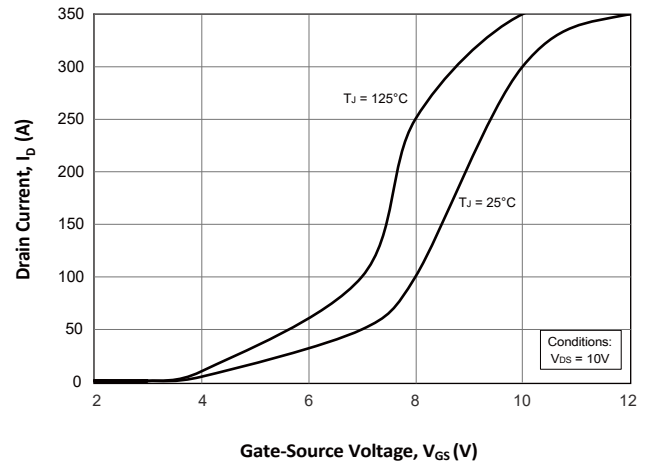
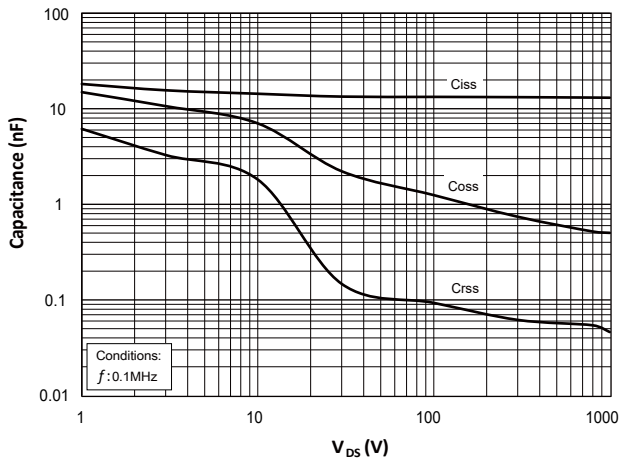
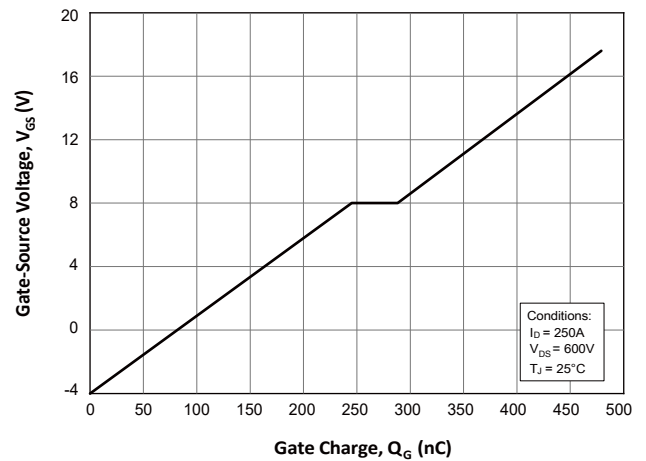
	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			

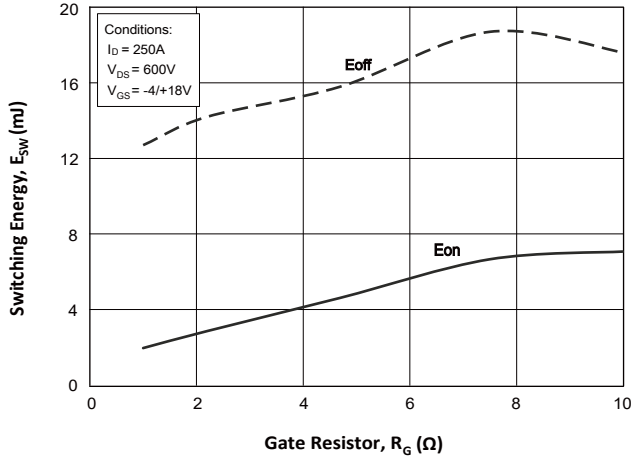
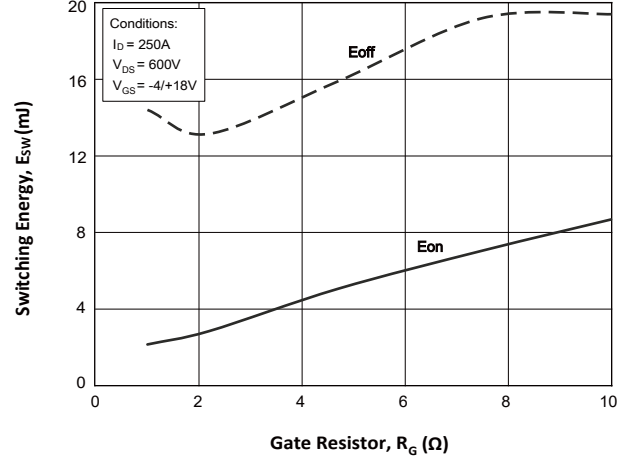
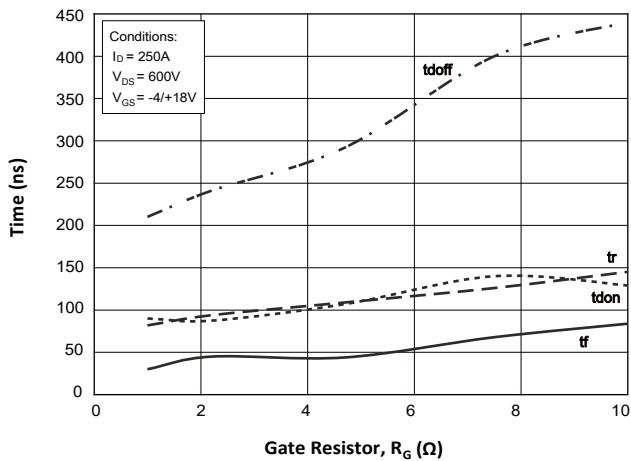
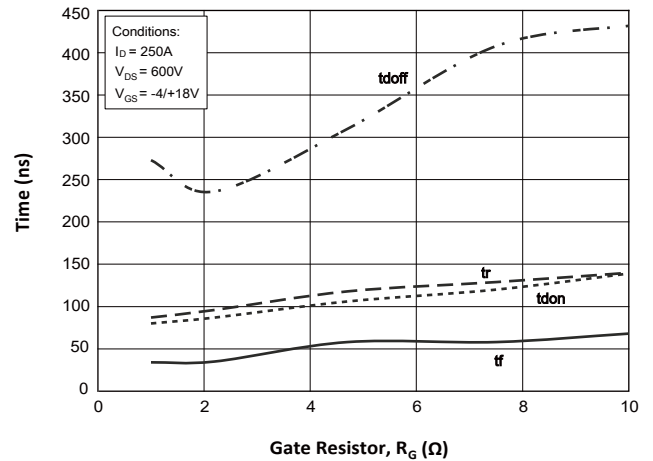
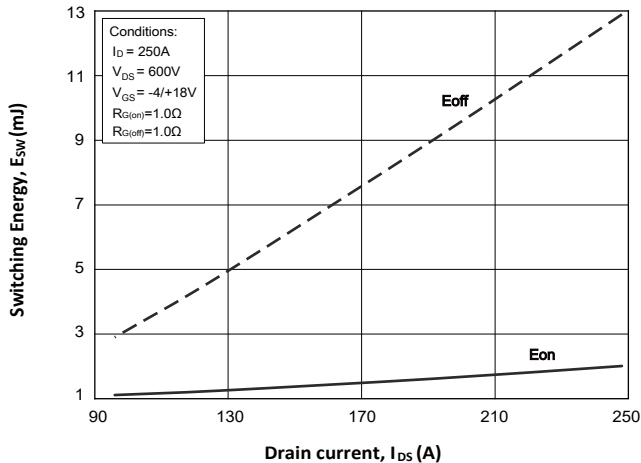
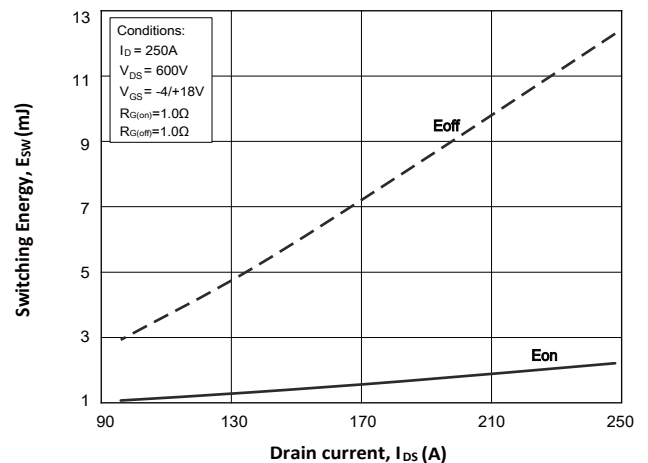
Electrical Characteristics @ $T_{VJ} = 25^{\circ}\text{C}$ (unless otherwise specified)

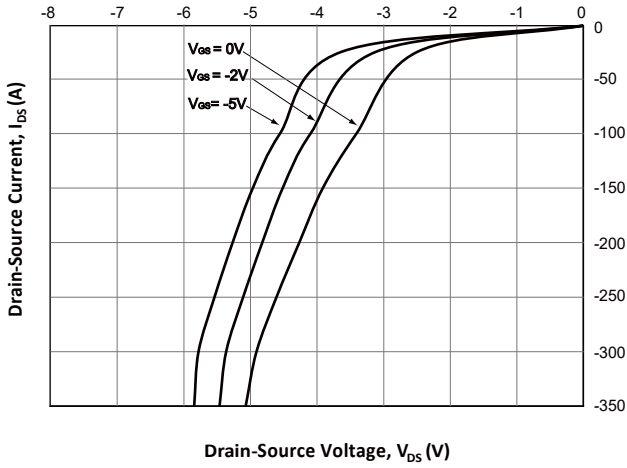
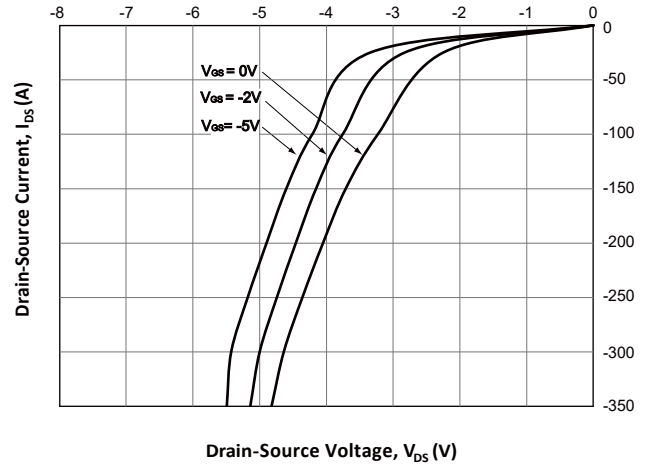
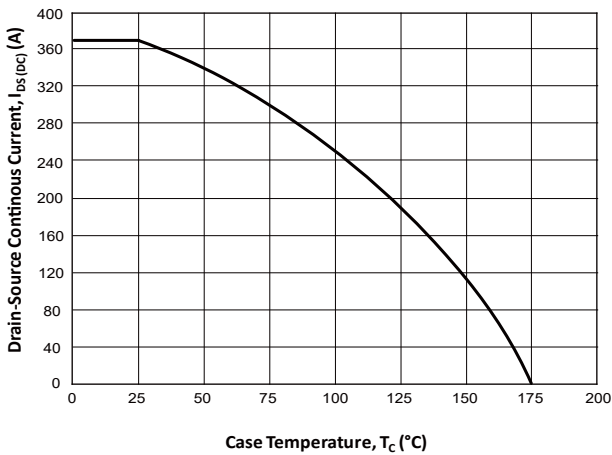
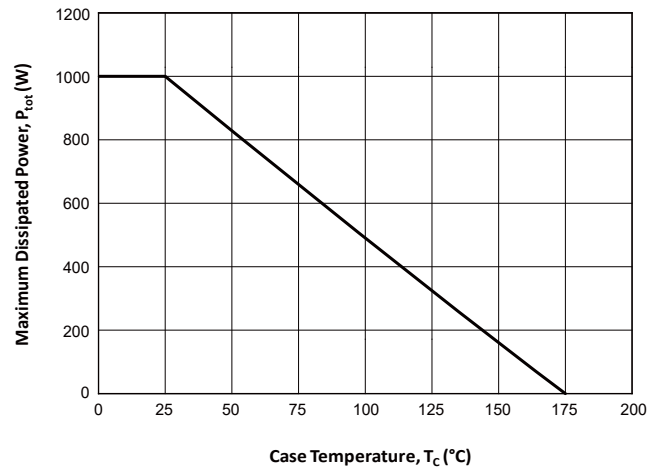
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
OFF Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_{DS} = 0.2mA$	1200	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = 1200V$	-	-	200	μA	
Gate-Body Leakage	I_{GSS}	$V_{GS} = 20V, V_{DS} = 0V$	-	-	500	nA	
ON Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = 100mA$	2.1	3.0	4.2	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 18V, I_{DS} = 100A$	-	6	7.8	m Ω	
Gate Resistance	$R_{G(int)}$	Internal gate resistor	$T_{VJ} = 25^{\circ}\text{C}$	3.77	-	Ω	
Dynamic Characteristics							
Input Capacitance	C_{iss}	$V_{DS} = 800V$	-	13.2	-	nF	
Output Capacitance	C_{oss}	$V_{GS} = 0V$ $V_{AC} = 1V$	-	0.53	-		
Reverse Transfer Capacitance	C_{rss}	Freq. = 100KHz	-	0.055	-		
Total Gate Charge	Q_g	$V_{DS} = 600V$	-	479	-	nC	
Gate to Source Charge	Q_{gs}	$V_{GS} = -4V/+18V$	-	245	-		
Gate to Drain Charge	Q_{gd}	$I_{DS} = 250A$	-	43	-		
Switching Characteristics							
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 600V$ $V_{GS} = -4V/+18V$ $I_{DS} = 250A$ $R_{G(on)} = 1.0\Omega$ $R_{G(off)} = 1.0\Omega$	$T_{VJ} = 25^{\circ}\text{C}$	-	80	-	ns
			$T_{VJ} = 150^{\circ}\text{C}$	-	80	-	
Rise Time	t_r		$T_{VJ} = 25^{\circ}\text{C}$	-	78	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	87	-	
Turn-Off Delay Time	$t_{d(off)}$		$T_{VJ} = 25^{\circ}\text{C}$	-	199	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	273	-	
Fall Time	t_f		$T_{VJ} = 25^{\circ}\text{C}$	-	23	-	
			$T_{VJ} = 150^{\circ}\text{C}$	-	34	-	
Turn-On Switching Energy	E_{on}		$T_{VJ} = 25^{\circ}\text{C}$	-	2.0	-	mJ
			$T_{VJ} = 150^{\circ}\text{C}$	-	2.2	-	
Turn-Off Switching Energy	E_{off}	$T_{VJ} = 25^{\circ}\text{C}$	-	11.9	-		
		$T_{VJ} = 150^{\circ}\text{C}$	-	14.4	-		
Body Diode Characteristics at $T_J = 25^{\circ}\text{C}$, unless otherwise specified							
Continuous Diode Fwd Current	I_{SDC}	$V_{GS} = 0V$	-	250	-	A	
Drain-Source Reverse Voltage	V_{SD}	$I_{SD} = 220A, V_{GS} = 0V$	-	4.4	-	V	
MOSFET Forward Recovery Charge	Q_{rr}	$V_{DD} = 600V$ $I_{SD} = 250A$ $V_{GS} = -4V/+18V$ $di/dt = 5200 A/\mu s$	$T_{VJ} = 25^{\circ}\text{C}$	-	268	-	nC
			$T_{VJ} = 150^{\circ}\text{C}$	-	2202	-	
MOSFET Peak Forward Recovery Current	I_{rrm}		$T_{VJ} = 25^{\circ}\text{C}$	-	24	-	A
			$T_{VJ} = 150^{\circ}\text{C}$	-	88	-	
MOSFET Reverse Recovery Time	T_{rr}		$T_{VJ} = 25^{\circ}\text{C}$	-	17	-	ns
			$T_{VJ} = 150^{\circ}\text{C}$	-	40	-	

Notes:

 1. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $> 2\%$.

Typical Characteristics
Fig.1 Output Characteristics at $T_J = 25^\circ\text{C}$

Fig.2 Output Characteristics at $T_J = 125^\circ\text{C}$

Fig.3 Drain Source on Resistance

Fig.4 Transfer Characteristics

Fig.5 Capacitances vs. Drain-Source Voltage

Fig.6 Gate Charge Characteristics


Typical Characteristics
Fig.7 Switching losses vs R_G change $T_J=125^\circ\text{C}$

Fig.8 Switching losses vs R_G change $T_J=150^\circ\text{C}$

Fig.9 Switching Timer vs R_G Change $T_J=125^\circ\text{C}$

Fig.10 Switching Timer vs R_G Change $T_J=150^\circ\text{C}$

Fig.11 Clamped Inductive Switching Energy vs. Drain Current $T_J=125^\circ\text{C}$

Fig.12 Clamped Inductive Switching Energy vs. Drain Current $T_J=150^\circ\text{C}$


Typical Characteristics
Fig.13 Body Diode curves $T_J = 25^\circ\text{C}$

Fig.14 Body Diode curves $T_J = 125^\circ\text{C}$

Fig.15 Continuous Drain Current (MOSFET) vs. Case Temperature

Fig.16 Max. Power Dissipation (MOSFET) Derating vs. Case Temperature


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